



Substitute for form 1449A/PTO
**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
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Complete if Known

Application Number	10/602,315
Filing Date	June 24, 2003
First Named Inventor	Ahn, Kie
Group Art Unit	2829
Examiner Name	Sarkar, Asok

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Attorney Docket No: 1303.107US1

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 * EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 608. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td colspan="2" style="text-align: center;"><small>Complete if Known</small></td> </tr> <tr> <td style="width: 60%;">Application Number</td> <td>10/602,315</td> </tr> <tr> <td>Filing Date</td> <td>June 24, 2003</td> </tr> <tr> <td>First Named Inventor</td> <td>Ahn, Kie</td> </tr> <tr> <td>Group Art Unit</td> <td>2829</td> </tr> <tr> <td>Examiner Name</td> <td>Sarkar, Asok</td> </tr> </table>	<small>Complete if Known</small>		Application Number	10/602,315	Filing Date	June 24, 2003	First Named Inventor	Ahn, Kie	Group Art Unit	2829	Examiner Name	Sarkar, Asok
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Substitute Disclosure Statement Form (PTO-1449)

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached